Santa Ana, CA
Microsemi
Progress Powered by Technology

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MSASC100W100H
MSASC100W100HR

100 Volts
100 Amps

LOW LEAKAGE SCHOTTKY DIODE

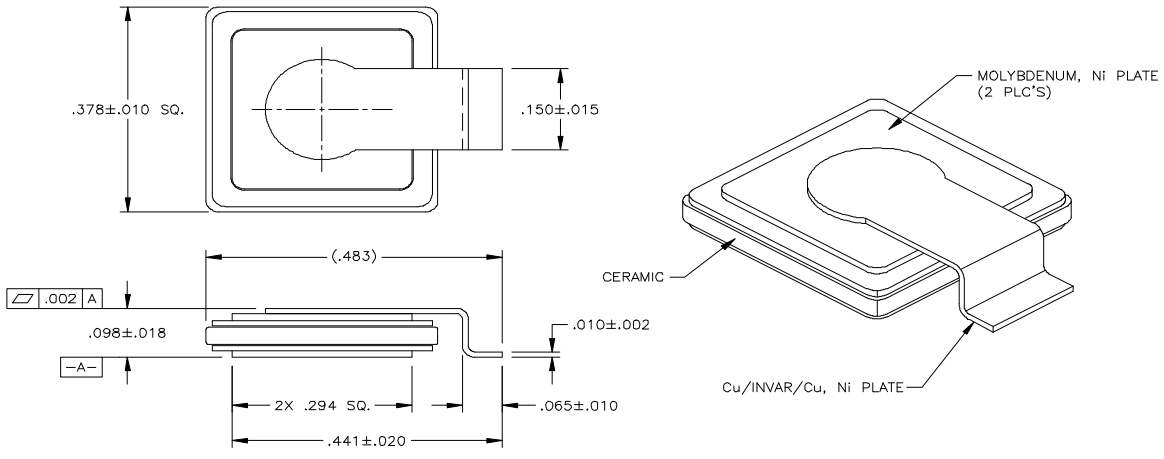
Features

- Tungsten schottky barrier
- Oxide passivated structure for very low leakage currents
- Guard ring protection for increased reverse energy capability
- Epitaxial structure minimizes forward voltage drop
- Hermetically sealed, low profile ceramic surface mount power package
- Low package inductance
- Very low thermal resistance
- Available as standard polarity (strap-to-anode, MSASC100W100H) and reverse polarity (strap-to-cathode: MSASC100W100HR)

Maximum Ratings @ 25°C (unless otherwise specified)

DESCRIPTION	SYMBOL	MAX.	UNIT
Peak Repetitive Reverse Voltage	V_{RRM}	100	Volts
Working Peak Reverse Voltage	V_{RWM}	100	Volts
DC Blocking Voltage	V_R	100	Volts
Average Rectified Forward Current, Tc≤ 135°C	$I_{F(ave)}$	100	Amps
derating, forward current, Tc≥ 135°C	dI_F/dT	2.5	Amps/°C
Nonrepetitive Peak Surge Current, tp= 8.3 ms, half-sinewave	I_{FSM}	500	Amps
Peak Repetitive Reverse Surge Current, tp= 1µs, f= 1kHz	I_{RRM}	2	Amp
Junction Temperature Range	T_j	-65 to +175	°C
Storage Temperature Range	T_{stg}	-65 to +175	°C
Thermal Resistance, Junction to Case: MSASC100W100H	θ_{JC}	0.35 0.5	°C/W

Mechanical Outline



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Electrical Parameters

DESCRIPTION	SYMBOL	CONDITIONS	MIN	TYP.	MAX	UNIT
Reverse (Leakage) Current	IR_{25}	VR= 100 Vdc, Tc= 25°C		.05	1	mA
	IR_{125}	VR= 100 Vdc, Tc= 125°C		10	100	mA
Forward Voltage pulse test, pw= 300 µs d/c≤ 2%	VF1	IF= 10A, Tc= 25°C		570	620	mV
	VF2	IF= 20A, Tc= 25°C		670	720	mV
	VF3	IF= 40A, Tc= 25°C		760	820	mV
	VF4	IF= 80A, Tc= 25°C		890	950	mV
	VF5	IF= 100A, Tc= 25°C		940		mV
	VF6	IF= 20A, Tc= -55°C		710	800	mV
	VF7	IF= 20A, Tc= 125°C		540		mV
Junction Capacitance	Cj1	VR= 10 Vdc		1500	2000	pF
	Cj2	VR= 5 Vdc		tbd		pF
Breakdown Voltage	BVR	IR= 1 mA, Tc= 25°C		120		V
		IR= 1 mA, Tc= -55°C	100	110		V